

Title (en)

METHOD FOR SELECTING FAULTY DIELECTRICS OF A SEMICONDUCTOR COMPONENT

Title (de)

VERFAHREN ZUM SELEKTIEREN FEHLERHAFTER DIELEKTRIKA EINES HALBLEITERBAUELEMENTES

Title (fr)

PROCEDE DE SELECTION DE DIELECTRIQUES DEFECTUEUX D'UN COMPOSANT A SEMI-CONDUCTEUR

Publication

**EP 1438742 A2 20040721 (DE)**

Application

**EP 02776786 A 20021007**

Priority

- DE 0203781 W 20021007
- DE 10149773 A 20011009

Abstract (en)

[origin: DE10149773A1] Process for selecting faulty dielectrics (2) of semiconductor component (1) comprises: forming a testing layer (3) during production of the component above dielectrics; simultaneously testing functionality of the dielectrics by applying electrical voltage on testing layer above and on substrate (4) below dielectrics; and removing or structuring testing layer to continue to production of component. Preferred Features: The testing layer is produced by intermediate structuring of the material layers already produced by the production process. The testing layer is made from polysilicon or polysilicon-germanium.

IPC 1-7

**H01L 21/66**

IPC 8 full level

**H01L 23/544** (2006.01)

CPC (source: EP)

**H01L 22/34** (2013.01); **H01L 2924/0002** (2013.01)

Citation (search report)

See references of WO 03034482A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)

**DE 10149773 A1 20030424**; EP 1438742 A2 20040721; TW 563220 B 20031121; WO 03034482 A2 20030424; WO 03034482 A3 20040129

DOCDB simple family (application)

**DE 10149773 A 20011009**; DE 0203781 W 20021007; EP 02776786 A 20021007; TW 91122928 A 20021004